

Assignment #1 ENEL469

1. Consider the following circuit where $V_{CC} = 6V$, $V_{EE} = -6V$, $\alpha = 0.9917356$, $R_C = 1k\Omega$, $R_B = 120k\Omega$, $R_E = 1.2k\Omega$, $V_{CE(Sat)} = 0.2V$, $V_A = 150V$, and $|V_{BE(on)}| = 0.7V$. Determine I_C and V_{CE} .

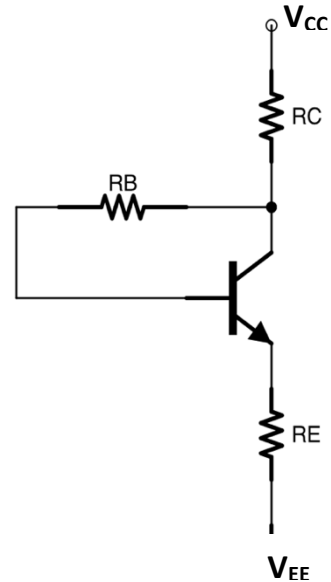
Soln:

Here, $\beta = \alpha / (1 - \alpha) = 120$

By KVL, $6 + 6 = I_E \times R_C + I_B \times R_B + V_{BE(on)} + I_E \times R_E$
 Or, $12 = (\beta + 1) \times I_B \times R_C + I_B \times R_B + 0.7 + (\beta + 1) \times I_B \times R_E$
 Or, $I_B = 29.26 \mu A$

Thus, $I_C = I_B \times \beta = 3.51 \text{ mA}$

By KVL, $V_{CE} = I_B \times R_B + V_{BE(on)}$
 Or, $V_{CE} = 4.21 \text{ V}$



2. Consider the following circuit where $V_{CC} = 10V$, $\beta = 140$, $R_C = 1k\Omega$, $R_B = 80k\Omega$, and $R_E = 1k\Omega$, $R_L = 2k\Omega$, $V_{CE(Sat)} = 0.2V$, $V_A = 150V$, and $|V_{BE(on)}| = 0.7V$. Determine I_C and V_{CE} .

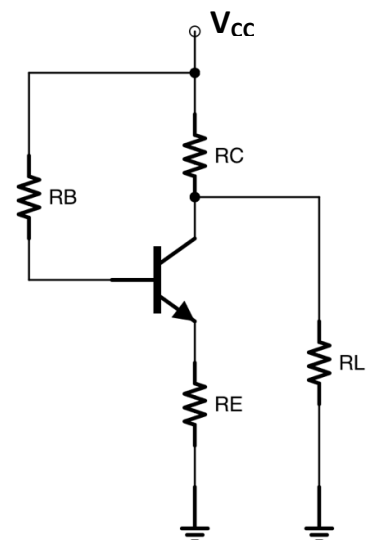
Soln:

By KVL, $V_{CC} = I_B \times R_B + V_{BE(on)} + (\beta + 1) \times I_B \times R_E$
 Or, $I_B = 42.08 \mu A$
 Thus, $I_C = I_B \times \beta = 5.93 \text{ mA}$

Here, the current in R_C will satisfy, $I_{RC} = I_C + I_{RL}$
 Thus, $I_{RC} < I_C$

Even considering, $I_{RC} = I_C$, V_{CE} becomes, $V_{CE} = -1.86 \text{ V}$.
 The above value indicates that the BJT is operating in saturation.

Thus, $V_{CE} = 0.2 \text{ V}$



To find the collector current let's assume $I_C \approx I_E$ for simplicity. Thus, we can consider the following equivalent circuit.

By KCL (nodal analysis)

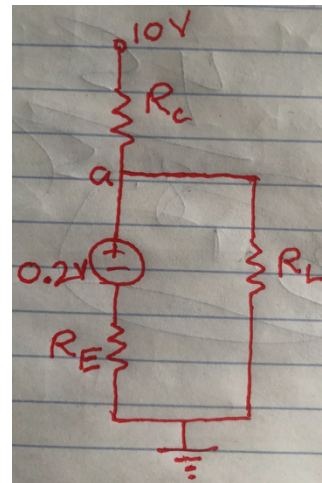
$$\frac{V_a - 10}{R_C} + \frac{V_a - 0.2}{R_E} + \frac{V_a}{R_L} = 0$$

$$\frac{V_a - 10}{1000} + \frac{V_a - 0.2}{1000} + \frac{V_a}{2000} = 0$$

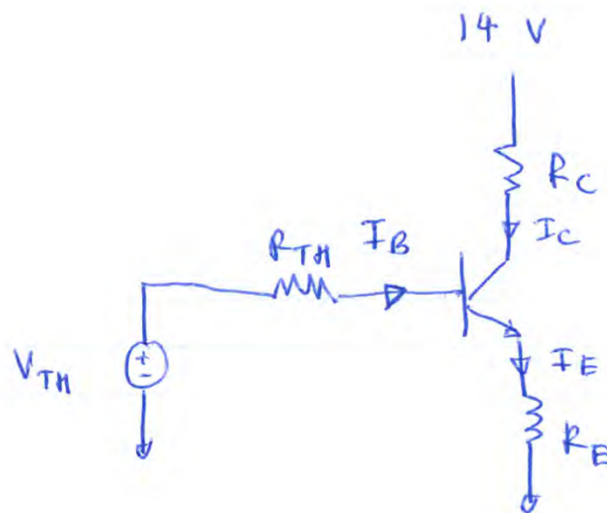
Or, $V_a = 4.08 \text{ V}$

Thus, $I_C \approx I_E = (V_a - 0.2)/1000$

Or, $I_C = 3.88 \text{ mA}$



3. Consider the following circuit where $V_{CC} = 14\text{V}$, $\beta = 60$, $R_C = 1\text{k}\Omega$, $R_1 = 60\text{k}\Omega$, $R_2 = 5\text{k}\Omega$, $R_E = 0.5\text{k}\Omega$, $V_{CE(\text{Sat})} = 0.2\text{V}$, $V_A = 150\text{V}$, and $|V_{BE(\text{on})}| = 0.7\text{V}$. Determine I_C and V_{CE} .



$$V_{TH} = \frac{V_{CC} \times R_2}{R_1 + R_2} = \frac{5}{65} \times 14 = \frac{14}{13} = 1.0769 \text{ V}$$

$$R_{TH} = \frac{R_1 R_2}{R_1 + R_2} = \frac{60 \times 10^3 \times 5 \times 10^3}{65 \times 10^3} = 4615.4 \Omega$$

$$V_B = V_{TH} - I_B R_{TH} = V_{BE} + I_E R_E$$

~~$V_{TH} - I_B R_{TH}$~~ Let assume operation ~~at~~ in active region.

$$V_{TH} - I_B R_{TH} = V_{BE} + (\beta + 1) I_B R_E$$

$$1.0769 - I_B \times 4615.4 = 0.7 + (60 + 1) I_B \times 500$$

$$I_B = 10.7338 \times 10^{-6} \text{ A}$$

$$I_C = \beta I_B = 60 I_B = 644.03 \times 10^{-6} \text{ A}$$

$$I_E = (\beta + 1) I_B = 61 I_B = 654.76 \times 10^{-6} \text{ A}$$

$$V_E = 500 \times I_E = 0.327 \text{ V}$$

$$V_C = 14 - 1000 \times I_C = 13.356 \text{ V}$$

$$V_{CE} = V_C - V_E = 13.029 \text{ V} > V_{CE(sat)}$$

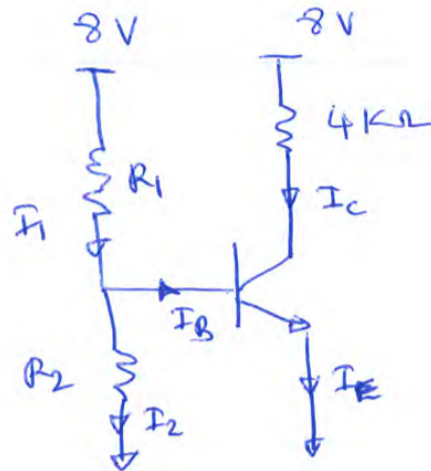
$$V_B = V_E + V_{BE} = 1.027 \text{ V}$$

$$V_{CB} = \cancel{V_C} V_C - V_B = 12.329 \text{ V} > 0$$

this confirms that the transistor operates in active region.

4. Consider the following circuit where $V_{CC} = 8V$, $\beta = 150$, $R_C = 4k\Omega$, $R_1 = 68k\Omega$, $R_2 = 8k\Omega$, $V_{CE(Sat)} = 0.2V$, $V_A = 200V$, and $|V_{BE(on)}| = 0.7V$. Determine I_C and V_{CE} .

(4)



$$R_1 = 68k\Omega$$

$$R_2 = 8k\Omega$$

$$V_{BE} = 0.7 = I_2 \times 8 \times 10^3$$

$$I_2 = 87.5 \times 10^{-6} A$$

$$8 = I_1 R_1 + I_2 R_2$$

$$I_1 = \frac{8 - I_2 R_2}{R_1}$$

$$I_1 = \frac{7.3}{68 \times 10^3} = 107.35 \times 10^{-6} A$$

$$I_1 = I_2 + I_B$$

$$I_B = I_1 - I_2 = 19.85 \times 10^{-6} A$$

if the circuit operates in active region

$$I_C = \beta I_B = 150 \times 19.85 \times 10^{-6}$$

$$= 2977.94 \times 10^{-6} A$$

$$V_{CE} = V_C - V_E = V_C = 8 - 4000 \times I_C$$

$$= -3.91 < 0$$

Since

$V_{CE} < 0$ ~~to~~ our assumption was wrong.

this circuit is in saturation.

$$V_{CE} = 0.2V = V_C = 8 - 4000 I_C$$

$$I_C = 1.95 \times 10^{-3} A //$$

5. Consider the following circuit where $V_{CC} = 12V$, $\beta = 60$, $R_C = 2k\Omega$, $R_1 = 45k\Omega$, $R_2 = 4k\Omega$, $V_{CE(sat)} = 0.2V$, $V_A = 200V$, and $|V_{BE(on)}| = 0.7V$. Assume that the maximum and minimum base currents are $I_{B(max)} = 150\mu A$ and $I_{B(min)} = 5\mu A$. Determine:
- The maximum and minimum values of R_C , satisfy the base current limits and the transistor operates in the active region. Assume all other values remain unchanged.
 - The maximum and minimum values of R_2 , satisfy the base current limits and the transistor operates in the active region. Assume all other values remain unchanged.
 - The maximum and minimum values of R_1 , satisfy the base current limits and the transistor operates in the active region. Assume all other values remain unchanged.

Soln:

With the given values, $I_{R2} = 175 \mu A$ and $I_{R1} = 251.1 \mu A$

Thus, $I_B = 251.1 - 175.0 = 76.1 \mu A$

And, $I_C = 4.57 mA$

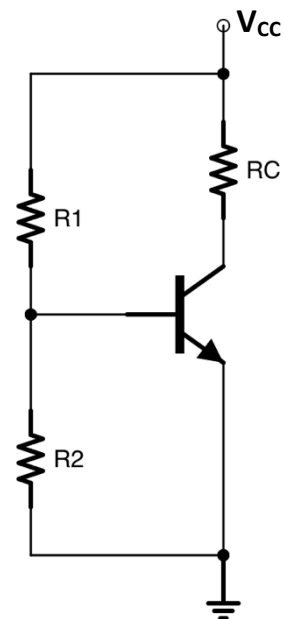
- a) If we change R_C only, the base current will not change

Thus, $R_{C(max)} = (V_{CC} - V_{CE,sat})/I_C$

Or, $R_{C(max)} = 11.8/4.57 mA$

Or, $R_{C(max)} = 2.58 k\Omega$

And $R_{C(min)} = 0 \Omega$



- b) If we change R_2 only (but not to zero), the base current will change but I_{R1} will remain unchanged.

With $R_C = 2 \text{ k}\Omega$, the maximum collector current is

$$I_{C(\max)} = (V_{CC} - V_{CE,\text{sat}})/R_C$$

Or, $I_{C(\max)} = 5.9 \text{ mA}$

Thus, $I_{B(\max)} = 98.33 \text{ }\mu\text{A}$. This indicates that for active region operation, the maximum base current should be $98.33 \text{ }\mu\text{A}$.

For $I_{B(\min)} = 5 \text{ }\mu\text{A}$, $R_{2(\min)}$ has to be

$$R_{2(\min)} = V_{BE(\text{on})}/[I_{R1} - I_{B(\min)}]$$

Or, $R_{2(\min)} = 0.7/(251.1 \text{ }\mu\text{A} - 5 \text{ }\mu\text{A})$

Or, $R_{2(\min)} = 2.84 \text{ k}\Omega$

For $I_{B(\max)} = 98.33 \text{ }\mu\text{A}$, $R_{2(\max)}$ has to be (i.e., active region operation)

$$R_{2(\max)} = V_{BE(\text{on})}/[I_{R1} - I_{B(\max)}]$$

Or, $R_{2(\max)} = 0.7/(251.1 \text{ }\mu\text{A} - 98.33 \text{ }\mu\text{A})$

Or, $R_{2(\max)} = 4.58 \text{ k}\Omega$

For $I_{B(\max)} = 150 \text{ }\mu\text{A}$, $R_{2(\max)}$ has to be (the transistor is in saturation though)

$$R_{2(\max)} = V_{BE(\text{on})}/[I_{R1} - I_{B(\max)}]$$

Or, $R_{2(\max)} = 0.7/(251.1 \text{ }\mu\text{A} - 150 \text{ }\mu\text{A})$

Or, $R_{2(\max)} = 6.92 \text{ k}\Omega$

- c) If we change R_1 only, the base current will change but I_{R2} will remain unchanged.

With $R_C = 2 \text{ k}\Omega$, the maximum collector current is

$$I_{C(\max)} = (V_{CC} - V_{CE,\text{sat}})/R_C$$

Or, $I_{C(\max)} = 5.9 \text{ mA}$

Thus, $I_{B(\max)} = 98.33 \text{ }\mu\text{A}$. This indicates that for active region operation, the maximum base current should be $98.33 \text{ }\mu\text{A}$.

Also, with $R_2 = 4 \text{ k}\Omega$ (given value), $I_{R2} = 0.7/4000 = 175 \text{ }\mu\text{A}$

For $I_{B(\min)} = 5 \text{ }\mu\text{A}$, $R_{1(\max)}$ has to be

$$R_{1(\max)} = [V_{CC} - V_{BE(\text{on})}] / [I_{R2} + I_{B(\min)}]$$

Or, $R_{1(\max)} = 62.78 \text{ k}\Omega$

For $I_{B(max)} = 98.33 \mu A$, $R_{1(min)}$ has to be (i.e., active region operation)

$$R_{1(min)} = [V_{CC} - V_{BE(on)}] / [I_{R2} + I_{B(max)}]$$

Or, $R_{1(min)} = 41.34 k\Omega$

For $I_{B(max)} = 150 \mu A$, $R_{1(min)}$ has to be (the transistor is in saturation though)

$$R_{1(min)} = [V_{CC} - V_{BE(on)}] / [I_{R2} + I_{B(max)}]$$

Or, $R_{1(min)} = 34.77 k\Omega$

6. Consider the following circuit where $V_{CC} = 20V$, $\beta = 100$, $V_{CE(Sat)} = 0.2V$, $V_A = 230V$, $|V_{BE(on)}| = 0.7V$. Design the circuit (Determine R_1 , R_2 , R_C , and R_E) so that the transistor operates at $V_{CE} = 6V$ and $I_C = 2.5mA$. Given that $R_C = R_E$ and $I_{R2} = 2I_B$.

Soln:

$$I_E = I_C \times (\beta + 1) / \beta = 2.525 \text{ mA}$$

By KVL, $V_{CC} = I_C \times R_C + V_{CE} + I_E \times R_E$

Or, $V_{CC} = I_C \times R_C + V_{CE} + I_E \times R_C$

Or, $20 = 2.5 R_C + 6 + 2.525 \times R_C$

Or, $R_C = 2.786 k\Omega$

And $R_E = 2.786 k\Omega$

Here, $I_B = I_C / \beta = 25 \mu A$

Thus, $I_{R2} = 50 \mu A$

And, $I_{R1} = 50 \mu A + 25 \mu A = 75 \mu A$

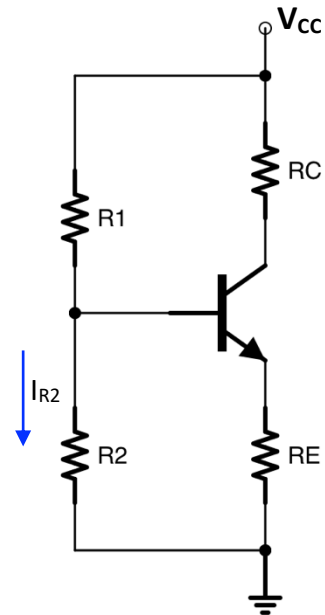
Thus, $R_2 = [V_{BE(on)} + I_E \times R_E] / I_{R2}$

Or, $R_2 = 154.7 k\Omega$

Also, $R_1 = [V_{CC} - I_{R2} \times R_2] / I_{R1}$

Or, $R_1 = 12.265 / 75 \mu A$

Or, $R_1 = 163.53 k\Omega$



7. Design the following circuit so that the transistors operate at $I_{C1} = 2\text{mA}$, $I_{C2} = 2\text{mA}$, $I_{C3} = 4\text{mA}$, $V_1 = 2\text{V}$, $V_2 = -3\text{V}$, and $V_3 = 0\text{V}$. Also given that $V_{CC} = 10\text{V}$, $V_{EE} = -10\text{V}$, $\beta = \infty$ (i.e., ignore base currents), $V_{CE(\text{Sat})} = 0.2\text{V}$, $V_A = 300\text{V}$, and $|V_{BE(\text{on})}| = 0.7\text{V}$.

Soln:

$$R_1 = (V_{CC} - V_1) / I_{C1}$$

Or, $R_1 = 4\text{ k}\Omega$

Again, $R_2 = (0 - 0.7 - V_{EE}) / I_{E1}$

Or, $R_2 = (0 - 0.7 + 10) / I_{E1}$

Or, $R_2 = 9.3 / 2\text{ mA}$

Or, $R_2 = 4.65\text{ k}\Omega$

Solving for R_3

$$R_3 = [V_{CC} - V_{BE2(\text{on})} - V_1] / I_{E2}$$

Or, $R_3 = [10 - 0.7 - 2] / 2\text{ mA}$

Or, $R_3 = 3.65\text{ k}\Omega$

Solving for R_4

$$R_4 = [V_2 - V_{EE}] / I_{C2}$$

Or, $R_4 = [-3 + 10] / 2\text{ mA}$

Or, $R_4 = 3.5\text{ k}\Omega$

Solving for R_5

$$R_5 = [V_{CC} - V_3] / I_{C3}$$

Or, $R_5 = 2.5\text{ k}\Omega$

Solving for R_6

$$R_6 = [V_2 - V_{BE3(\text{on})} - V_{EE}] / I_{E3}$$

Or, $R_6 = 6.3 / 4\text{ mA}$

Or, $R_6 = 1.575\text{ k}\Omega$

